



USPTO-1488

December 15, 2003

To: Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
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Subject: | Serial No. 10/666,359 09/19/03 |

Chi-Chun Chen et al.

METHOD OF FORMING AN ULTRATHIN  
NITRIDE/OXIDE STACK AS A GATE  
DIELECTRIC

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

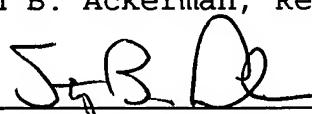
The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
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P.O. Box 1450, Alexandria, VA 22313-1450, on December 19, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 12/19/03

U.S. Patent 6,228,779 to Bloom et al., "Ultra Thin Oxynitride and Nitride/Oxide Stacked Gate Dielectrics Fabricated by High Pressure Technology," describes an SiON and ON stack gate dielectric high pressure process.

U.S. Patent 6,017,791 to Wang et al., "Multi-Layer Silicon Nitride Deposition Method for Forming Low Oxidation Temperature Thermally Oxidized Silicon Nitride/Silicon Oxide (NO) Layer," describes an ON process for a gate dielectric.

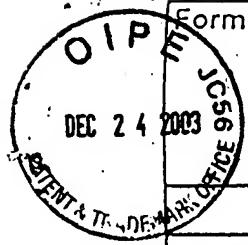
U.S. Patent 6,020,238 to He et al., "Method of Fabricating a High Dielectric Constant Interpolysilicon Dielectric Structure for a Low Voltage Non-Volatile Memory", describes a high-k (high dielectric constant) gate dielectric process for a low voltage non-volatile memory.

U.S. Patent 5,464,792 to Tseng et al., "Process to Incorporate Nitrogen at an Interface of a Dielectric Layer in a Semiconductor Device," describes a process to incorporate nitrogen at an interface of a dielectric layer in a semiconductor device.

Sincerely



Stephen B. Ackerman,  
Reg. No. 37761



~~Form PTO-1449~~

## INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

**Doctor Number (Spain)**

Apples on Mandate

TSMC-01-1488

10/666, 359

Appl. Sci. 2021, 11, 3330

Filing Date

09/19/03

Group Art Unit

U. S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

**OTHER DOCUMENTS** (Including Author, Title, Date, Portion or Pages, Etc.)


**EXAMINER**

**DATE CONSIDERED**

**EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.